CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the U.S. Postal Service with sufficient as first class mail in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.G. 20231, on April 11, 2002.

Signature:

Reluced A BAUMAPP

Attorney Docket No. NTI-019-2

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application)	PATENT APPLICATION			
Inventor(s): Christophe Pierrat et al.)	Art Unit: 2812	Œ		
Application No.: 09/675,197)	· · · · · · · · · · · · · · · · · · ·	SE SE		
Filed: 09/29/2000)	Examiner: unknown	ECHNOLOGY	Nob I	REC
Title Dissection Of Edges With Projection Points In A Fabrication Layout For Correcting Proximity Effects)	: :	CENTER	7 20 <u>0</u> 2	EIVED
Litetis		: ; :- <u></u>	2800		

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Assistant Commissioner for Patents Washington, D.C. 20231

Sir:

Listed below or on an attached Form PTO-1449 is information known to applicant(s). A copy of each listed publication and U.S. and foreign patent, except for pending U.S. applications, is being submitted herewith, along with a concise explanation of information in a foreign language, if any, pursuant to 37 C.F.R. §1.97-1.98.

Applicants respectfully request that the listed information be considered by the Examiner and be made of record in the above-identified application. If form PTO-1449 is enclosed, the Examiner is requested to initial and return it in accordance with MPEP § 609.

This statement is not intended to represent that a search has been made or that the information cited in the statement is, or is considered to be, material to patentability as defined in 37 C.F.R. § 1.56.

\boxtimes	This s	tatemen	t qualifies under 37 C.F.R. § 1.97, s	ubsection (b) because (check all that apply):	
		(1)	prosecution application u	of the application filing date and is other than a continued under § 1.53(d)	
		(2)	OR It is being filed within 3 months of the control of the c	of entry of a national stage	
	\boxtimes	(3)		ate of the first Office Action on the merits.	
		(4)		g of a first Office Action after the filing of a request for nder § 1.114	
	date o	f the ear		d after the period specified in § 1.97(b), but before the mailing 1.113, a notice of allowance under § 1.311, or an action that nen:	
		a certi	ification as specified in § 1.97(e) is	provided below; or	
			of \$180.00 as set forth in § 1.17(p) appears filed together with this states	is authorized below, enclosed, or included with the payment of ment.	
	37 C.F.R. § 1.97(d). If this statement is being filed after the period specified in § 1.97(c), but on or before payment of the issue fee, then:				
	A.	a certi	ification as specified in § 1.97(e) is	completed below; and	
	B.		of \$180.00 as set forth in § 1.17(p) papers filed together with this states	is authorized below, enclosed, or included with the payment of ment.	
	charge	e any ad		authorized to charge the above-referenced fees of \$ 180 and nent associated with this communication to Deposit Account	
				Respectfully submitted,	
			:	BEVER, HOFFMAN & HARMS, LLP	
Dated:	4	1 - //	· 0Z	Ву:	
				Jeanette S. Harms, Reg. No. 35,537	
Teleph	•	08) 451- 29477	-5900		



INFORMATION DISCLOSURE CITATION

PTO-1449

Atty. Docket No.

Serial No.

NTI-019-2

09/675,197

Applicant

PIERRAT, Christophe

Filing Date

Group

9/29/2000

2812

U.S. PATENT DOCUMENTS

		U.S. PATENT DOCUMENTS				
EXAMINER'S INITIALS	PATENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE
	4,426,584	1/17/1984	Bohlen, et al.	250	492.2	6/3/1981
	4,895,780	1/23/1990	Nissan-Cohen, et al.	430	5	10/25/1988
	5,208,124	5/4/1993	Sporon-Fiedler, et al.	430	5	3/19/1991
	5,682,323	10/28/1997	Pasch, et al.	364	491	3/6/1995
٥.	5,958,635	9/28/1999	Reich, et al.	430	30	10/20/1997
	5,972,541	10/26/1999	Sugasawara, et al.	430	5	3/4/1998
	6,007,310	12/28/1999	Jacobsen, et al.	417	362	5/23/1997
	6,114,071	9/5/2000	Chen, et al.	430	5	4/6/1998
	6,289,499	9/11/2001	Rieger, et al.	716	21	1/7/2000
	6,249,597 B1	6/19/2001	Tsudaka	382	144	12/17/1998

)O

Date Considered:

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP § 609; draw line through citation if not in conformance <u>and</u> not considered. Include copy of this form with next communication to applicant.

EXAMINER:

				Atty. Docket No. NTI-019-2	Seria	l No. 0/675,197		
	INFORMATION DISCLOSURE CITATION OIPE PTO-1449		Applicant PIERRAT, Christ		7073,177			
/			Filing Date	Group	•			
00/1	APR 1 5 200	(بېر 2		9/29/2000	28	312		
′	PADEMARY	N. C.	FO	REIGN PATENT DOCU	JMENTS			
	EXAMINER'S INITIALS	PATENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSL	ATION NO
	<i>1</i> 2	3-80525	4/5/1991	JP				
		2,324,169 A	10/14/1998	GB				
		WO 99/47981	9/23/1999	wo			П	П

APR 17 2002 TECHNOLOGY CENTER 2800

EXAMINER:	Date Considered:	

INFORMATION DISCLOSURE
CITATION

PTO-1449

Atty. Docket No.

Serial No.

NTI-019-2

09/675,197

Applicant

PIERRAT, Christophe

Filing Date

Group

9/29/2000

2812

RADEMARY	OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)
EXAMINER'S INITIALS	CITATION
\	Choi, Y., et al., "Optical Proximity Correction on Attenuated Phase Shifting Photo Mask for Dense Contact Array", LG Semicon Company (11 pages).
	Lucas, K., et al., "Model Based OPC for 1st Generation 193nm Lithography", Motorola Inc., IDT assignee to IMEC (12 pages).
	Stirniman, J., et al., "Quantifying Proximity and Related Effects in Advanced Wafer Processes", Precim Compnay, Hewlett Packard Labs (9 pages).
	Sugawara, M., et al., "Practical Evaluation of Optical Proximity Effect Correction by EDM Methodology", Sony Corporation (11 pages).
	Granik, Y., et al., "MEEF as a Matrix", Mentor Graphics Corporation (11 pages).
,	Kang, D., et al., "Effects of Mask Bias on t he Mask Error Enhancement Factor (MEEF) of Contact Holes" (11 pages).
	Matsuura, S., et al., "Reduction of Mask Error Enhancement Factor (MEEF) by the Optimum Exposure Dose Self-Adjusted Mask", NEC Corporation (12 pages).
	Fu, C.C., et al., "Enhancement of Lithographic Patterns by Using Serif Features", IEEE, Transactions On Electron Devices, Vol. 38, No. 12, pp. 2599-2603, December 1991.
•	Henderson, R., et al., "Optical Proximity Effect Correction: An Emerging Technology", Microlithography World, pp. 6-12 (1994).
	Dolainsky, C., et al., "Application of a Simple Resist Model to Fast Optical Proximity Correction", SPIE, Vol. 3051, pp. 774-780 (1997).
	Chen, J., et al., "Full-Chip Optical Proximity Correction with Depth of Focus Enchancement", Microlithography World ,(5 pages) (1997).
	Wong, A., et al., "Lithographic Effects of Mask Critical Dimension Error", SPIE, Vol. 3334, pp. 106-115 (1998).
	Balasinski, A., et al., "Comparison of Mask Writing Tools and Mask Simulations for 0.16um Devices", IEEE, SEMI Advanced Semiconductor Manufacturing Conference, pp. 372-377 (1999).

EXAMINER:	Date Considered:	TECHNOLOGY VPK I
EXAMINER: Initial if reference considered, whether or not MPEP § 609; draw line through citation if not in conformatopy of this form with next communication to applicant.		 CENTER NTI Use Only: 7TI: 24; 1

13